February 9, 2005

RF Micro Devices Opens Customer Support and Design Center in Toulouse, France

New Office to Support Collaboration between RFMD and Leading Wireless Manufacturers in the Development of Next-Generation EDGE and WCDMA Products

GREENSBORO, N.C.--(BUSINESS WIRE)--Feb. 9, 2005--RF Micro Devices, Inc. (NASDAQ: RFMD), a leading provider of proprietary radio frequency integrated circuits (RFICs) for wireless communications applications, today announced the opening of a new customer support and design center in Toulouse, France. The office was established to support collaboration between RFMD and leading wireless manufacturers located in Toulouse and other parts of Europe. The office will focus on the development of next-generation EDGE and WCDMA cellular products, including RFMD's POLARIS™ 2 TOTAL RADIO™ transceiver and module solutions.

Eric Creviston, corporate vice president of wireless products, RF Micro Devices, said, "We are extremely pleased to announce the establishment of our Toulouse customer support and design center, which draws upon the significant wireless communications expertise in the Toulouse area. Our new office was instrumental in the launch of our POLARIS 2 TOTAL RADIO product portfolio and will also support other next-generation cellular solutions. We expect this office will further accelerate customer adoption of RFMD's EDGE and WCDMA transceiver and power amplifier solutions, and will also serve to provide our customers with additional local support."

Nadim Khlat, staff system engineer, RF Micro Devices, said, "The Toulouse customer support and design center is staffed by a team of talented applications engineers, system engineers and technicians primarily focused on developing radio solutions for 2.5G and 3G standards and providing direct support to our customers. We expect the new design center team will further enhance collaboration between RFMD and those leading wireless manufacturers who are increasingly selecting our POLARIS TOTAL RADIO solutions."

RFMD's Toulouse design center is located in Parc Le Millenaire at Blagnac, Avenue Escadrille Normandie-Niemen, 31700 Blagnac.

RF Micro Devices, Inc., an ISO 9001- and ISO 14001-certified manufacturer, designs, develops, manufactures and markets proprietary radio frequency integrated circuits (RFICs) for wireless communications products and applications. The Company is a leading supplier of power amplifiers, one of the most critical radio frequency (RF) components in cellular phones. The Company is also the leading manufacturer of GaAs HBT, which offers distinct advantages over other technologies for the manufacture of current- and next-generation power amplifiers. The Company's products are included primarily in cellular phones, base stations, wireless local area networks (WLANs), cable television modems and global positioning systems (GPS). The Company derives revenue from the sale of standard and custom-designed products. The Company offers a broad array of products including amplifiers, mixers, modulators/demodulators and single-chip transmitters, Bluetooth® products and receivers and transceivers that represent a substantial majority of the RFICs required in wireless subscriber equipment. The Company's goal is to be the premier supplier of low-cost, high-performance integrated circuits and solutions for applications that enable wireless connectivity. RF Micro Devices, Inc., is traded on the Nasdaq National Market under the symbol RFMD. For more information about RFMD, please visit www.rfmd.com.

This press release contains forward-looking statements that relate to RF Micro Devices' plans, objectives, estimates and goals. Words such as "expects," "anticipates," "intends," "plans," "projects," "believes" and "estimates," and variations of these words and similar expressions, identify these forward-looking statements. RF Micro Devices' business is subject to numerous risks and uncertainties, including variability in quarterly operating results, the rate of growth and development of wireless markets, risks associated with the operation of wafer fabrication, molecular beam epitaxy and other foreign and domestic manufacturing facilities, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, our ability to reduce costs and improve gross margins by implementing innovative technologies, our ability to bring new products to market, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on a limited number of customers and dependence on third parties. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

CONTACT: RF Micro Devices, Inc.
Jerry Neal, 336-664-1233

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